

# **N-Channel Power MOSFET**

 $600V, 4A, 0.9\Omega$ 

#### **FEATURES**

- Super-Junction technology
- · High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance
- 100% UIL tested
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER VALUE UNIT				
$V_{DS}$	600	V		
R <sub>DS(on)</sub> (max)	0.9	Ω		
$Q_g$	9.6	nC		





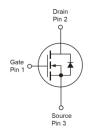


#### **APPLICATIONS**

- Power Supply
- Lighting







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	600	V
Gate-Source Voltage		V <sub>GS</sub>	±30	V
Continuous Drain Current (Note 1)	T <sub>C</sub> = 25°C		4	А
	T <sub>C</sub> = 100°C	I <sub>D</sub>	2.4	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	12	А
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	36.8	W
Single Pulsed Avalanche Energy (Not	e 3)	E <sub>AS</sub>	42.3	mJ
Single Pulsed Avalanche Current (No	te 3)	I <sub>AS</sub>	1.3	А
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	$R_{\Theta JC}$	3.4	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	3.3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Drain-Source On-State Resistance (Note 4)	V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.2A	R <sub>DS(on)</sub>		0.69	0.9	Ω
Dynamic (Note 5)	l	1	L	•		
Total Gate Charge	$V_{DS} = 380V, I_D = 4A,$	Qg		9.6		nC
Gate-Source Charge		Q <sub>gs</sub>		2.0		
Gate-Drain Charge	$V_{GS} = 10V$	$Q_{gd}$		4.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C <sub>iss</sub>		315		
Output Capacitance	f = 1.0MHz	C <sub>oss</sub>		46.4		pF
Gate Resistance	F = 1MHz, open drain	$R_g$		3.2		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4A, V_{GS} = 10V,$	t <sub>d(on)</sub>		18		
Turn-On Rise Time		t <sub>r</sub>		10		
Turn-Off Delay Time		t <sub>d(off)</sub>		36.4		ns
Turn-Off Fall Time	1D = 4A, VGS = 10V,	t <sub>f</sub>		8		]
Source-Drain Diode						
Forward Voltage (Note 4)	I <sub>S</sub> = 4A, V <sub>GS</sub> = 0V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	$V_R = 100V, I_S = 4A$	t <sub>rr</sub>		185.5		ns
Reverse Recovery Charge	$dI_{F}/dt = 100A/\mu s$	Q <sub>rr</sub>		1.38		μC

#### Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 50mH,  $I_{AS} = 1.3A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 4. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.

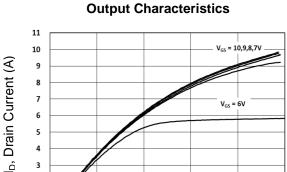
## **ORDERING INFORMATION**

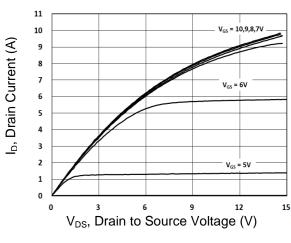
PART NO.	PACKAGE	PACKING
TSM60NB900CH C5G	TO-251 (IPAK)	75pcs / Tube

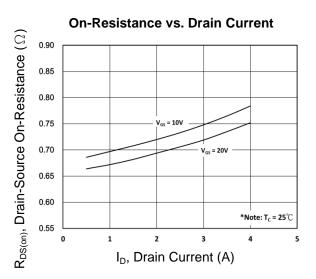


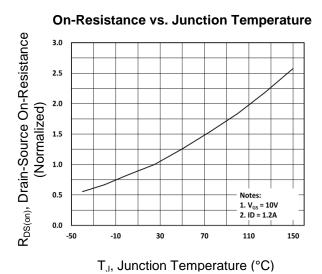
#### **CHARACTERISTICS CURVES**

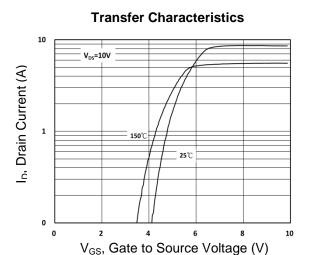
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

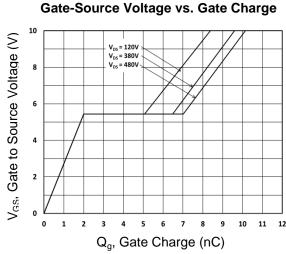


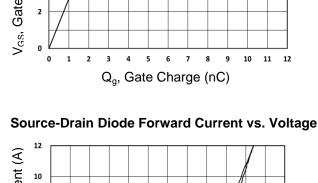


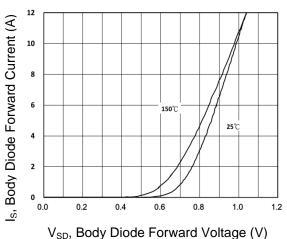












Version: A1608

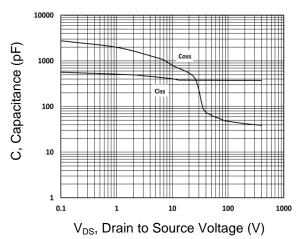
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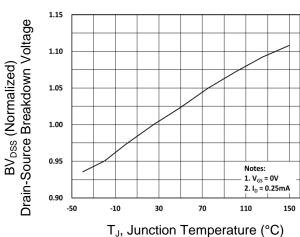
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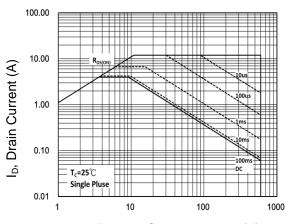
## Capacitance vs. Drain-Source Voltage



## BV<sub>DSS</sub> vs. Junction Temperature

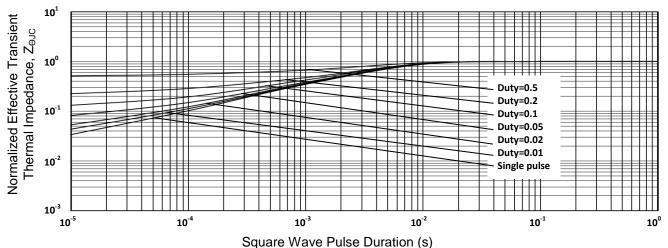


#### **Maximum Safe Operating Area**



# $V_{\text{DS}}$ , Drain to Source Voltage (V)

#### Normalized Thermal Transient Impedance, Junction-to-Case

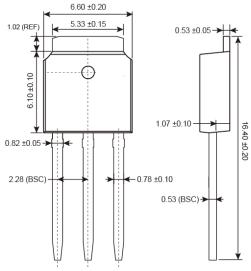


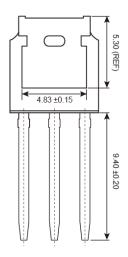




# PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

# TO-251 (IPAK)





## **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

 $\mathbf{O}$  =Jan  $\mathbf{P}$  =Feb  $\mathbf{Q}$  =Mar  $\mathbf{R}$  =Apr

S =May T =Jun U =Jul V =Aug
W =Sep X =Oct Y =Nov Z =Dec

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L = Lot Code (1~9, A~Z)



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